



MMBT3904FZ

40V NPN SMALL SIGNAL TRANSISTOR IN DFN0606

Features

- $BV_{CEO} > 40V$
- I_C = 200mA High Collector Current
- P_D = 925mW Power Dissipation
- 0.36mm² Package Footprint, 40% Smaller than DFN1006
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type MMBT3906FZ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

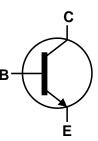
- Case: X2-DFN0606-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208@4
- Weight: 0.0008 grams (Approximate)



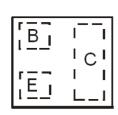




Bottom View



Device Symbol



Top View **Device Schematic**

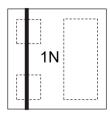
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3904FZ-7B	1N	7	8mm	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



Top View Bar Denotes Base and Emitter Side

1N = Product Type Marking Code



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ic	200	mA
Peak Pulse Collector Current	I _{CM}	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	270		mW	
Fower Dissipation	(Note 6)	P _D	925	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	465		°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	135	C/VV	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	135	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

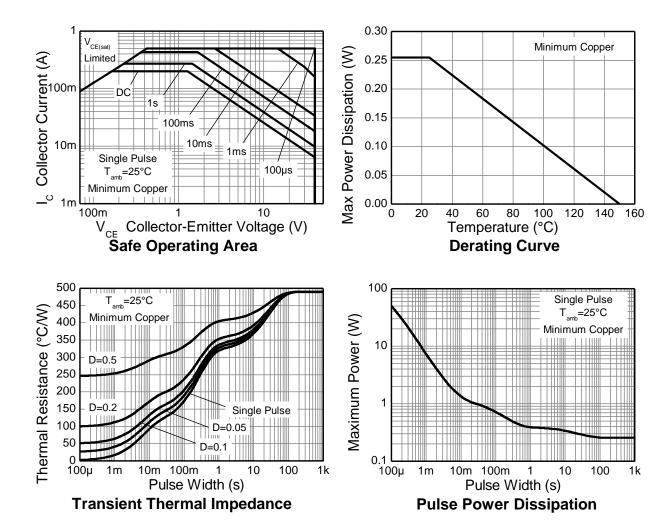
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured The device mounted of minimum recommended pad layout 102 copper that is of a single-sided 1.5mm FR4 PCB, device is a under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
 Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
 Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)		40	_	V	$I_C = 10.0 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage		6.0	_	٧	$I_E = 100\mu A, I_C = 0$	
Collector Cutoff Current	I _{CEX}		50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V	
Base Cutoff Current	I _{BL}	1	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V	
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	l	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 1.0 V \\ I_C &= 1.0 m A, \ V_{CE} = 1.0 V \\ I_C &= 10 m A, \ V_{CE} = 1.0 V \\ I_C &= 50 m A, \ V_{CE} = 1.0 V \\ I_C &= 100 m A, \ V_{CE} = 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	l	0.20 0.30	٧	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA	
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.65 —	0.85 0.95	V	$I_C = 10mA, I_B = 1.0mA$ $I_C = 50mA, I_B = 5.0mA$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$	
Input Capacitance	C _{ibo}	_	9.5	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$	
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_C = 10mA,$ f = 100MHz	
SWITCHING CHARACTERISTICS						
Delay Time	t _d	1	35	ns	$V_{CC} = 3.0V, I_C = 10mA,$ $V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$	
Rise Time	t _r	1	35	ns		
Storage Time	prage Time t_s — 200 ns $V_{CC} = 3.0V$, $I_C = 10$ n		V _{CC} = 3.0V, I _C = 10mA,			
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$	

Note:

9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.~$ Duty cycle $\leq 2\%.$



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

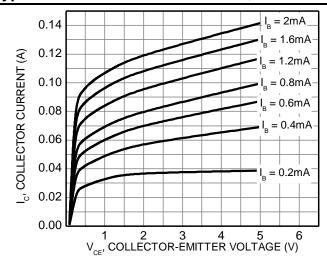


Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

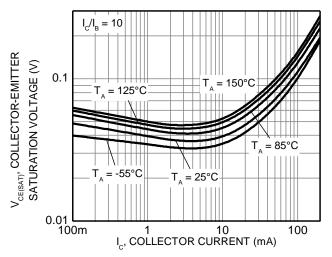


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

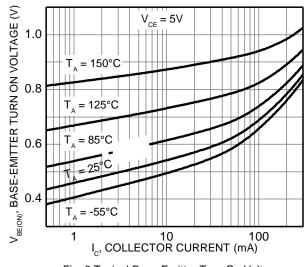


Fig. 8 Typical Base-Emitter Turn On Voltage vs. Collector Current

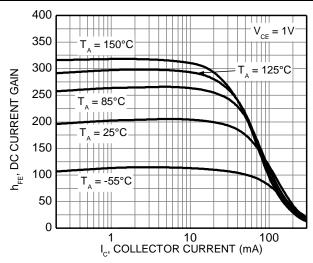


Fig. 5 Typical DC Current Gain vs. Collector Current

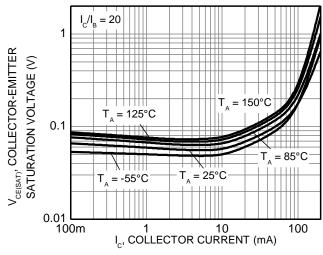


Fig. 7 Typical Collector-Emitter Saturation Voltage vs. Collector Current

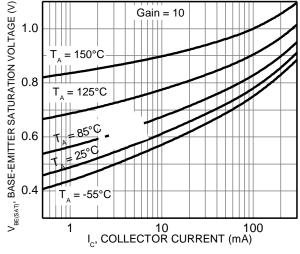
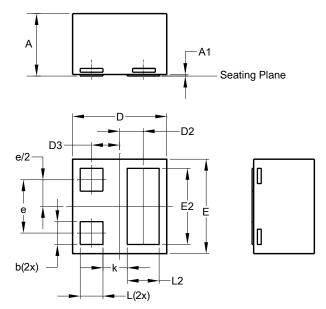


Fig. 9 Typical Base-Emitter Saturation Voltage vs. Collector Current



Package Outline Dimensions

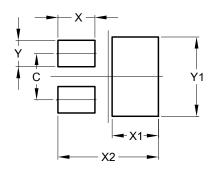
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN0606-3				
Dim	Min	Max	Тур	
Α	0.36	0.42	0.39	
A1	0	0.05	0.02	
b	0.10	0.20	0.15	
D	0.57	0.67	0.62	
D2	0.155 BSC			
D3	0	.185 BS	С	
Е	0.57	0.67	0.62	
E2	0.40	0.60	0.50	
е	0.35 BSC			
k	0.16 REF			
L	0.09	0.21	0.15	
L2	0.11	0.31	0.21	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.350		
Х	0.280		
X1	0.350		
X2	0.760		
Y	0.200		
Y1	0.600		



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